L Number	Hits		DB	Time stamp	
387	871	(438/238).CCLS.	USPAT;	2003/12/09 09:4	2
			US-PGPUB; EPO; JPO;		
			DERWENT;		:
			: IBM_TDB		ĺ
388	269	((438/238).CCLS.) and (SRAM or(static near	USPAT;	: 2003/12/09 09:1	.2
300	260	random near access near memory))	US-PGPUB	: 2002/12/00 00.1	:
389	209	((438/238).CCLS.) and (SRAM or(static near random near access near memory))	USPAT; US-PGPUB;	2003/12/09 09:1	. 3
		random near access near memory,	EPO; JPO;		
			DERWENT;		;
	_ !	·	IBM_TDB		1
390 391	3	("5330930" "5365104" "5877059").PN. (257/903).CCLS.	USPAT;	2003/12/09 09:2	1
391	774	(2377 903) . CCL3.	US-PGPUB;	2003/12/09 09:4	
			EPO; JPO;	•	:
			DERWENT;		1
	21245	ODDW 4 + + +	IBM_TDB	0000/10/00 00 1	
- '	31345	SRAM (static near random near access near memory)	USPAT; US-PGPUB	2003/12/09 09:1	.2
_	26244	(SRAM (static near random near access near	USPAT;	2003/12/08 14:1	3
1		memory)) and (trench via contact open\$)	US-PGPUB		'
-	26208	(SRAM (static near random near access near	USPAT;	2003/12/08 14:1	4
!	E 0.00	memory)) and (trench via contact open\$3)	US-PGPUB	2002/12/02 11	
-	5928	((SRAM (static near random near access near memory)) and (trench via contact	USPAT;	2003/12/08 14:1	. 5
!		open\$3)) and etch\$3	03.50500	i	i
-	4948		USPAT;	2003/12/08 14:1	15
		near memory)) and (trench via contact	US-PGPUB	!	
!	4050	open\$3)) and etch\$3) and (source drain)		0002/10/00 14:1	i
, -	4059	((((SRAM (static near random near access near memory)) and (trench via contact	USPAT; US-PGPUB	2003/12/08 14:1	-0
		open\$3)) and etch\$3) and (source drain))	i ob rarob		ŀ
		and resist\$6			:
-	3615	(((((SRAM (static near random near access	'USPAT;	2003/12/08 14:1	۱6
:		near memory)) and (trench via contact	US-PGPUB		i
		open\$3)) and etch\$3) and (source drain)) and resist\$6) and gate	1	1	
-	3349	((((((SRAM (static near random near access	USPAT;	2003/12/08 14:1	L7
		near memory)) and (trench via contact	US-PGPUB		
i		open\$3)) and etch\$3) and (source drain))			;
_	76	and resist\$6) and gate) and transistor ((((((SRAM (static near random near	USPAT;	2003/12/08 14:1	17
	70	access near memory)) and (trench via	US-PGPUB	:	٠
		contact open\$3)) and etch\$3) and (source	i	i I	
		drain)) and resist\$6) and gate) and			į
j		transistor) and (horizontal near10			-
_	280	transistor) (((((((SRAM (static near random near	USPAT;	; 2003/12/08 17:4	13
	200	access near memory)) and (trench via	US-PGPUB		. •
		contact open\$3)) and etch\$3) and (source	1		1
		drain)) and resist\$6) and gate) and		•	
		transistor) and ((pull?down (pull near3 down)) near10 transistor)			
	42124	SRAM (static near random near access near	USPAT;	; 2003/12/08 17:4	13
	•	memory)	US-PGPUB;		i
į			EPO; JPO;	!	ļ
İ			DERWENT;		i
	283	///////SRAM (static near random near	IBM_TDB	2003/12/08 18:2	29
-	283	<pre>(((((((SRAM (static near random near access near memory)) and (trench via</pre>		2003/12/08 18:2	29
-	283	access near memory)) and (trench via contact open\$3)) and etch\$3) and (source	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/12/08 18:2	29 i
-	283	access near memory)) and (trench via contact open\$3)) and etch\$3) and (source drain)) and resist\$6) and gate) and	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/08 18:2	29
-	283	access near memory)) and (trench via contact open\$3)) and etch\$3) and (source drain)) and resist\$6) and gate) and transistor) and ((pull?down (pull near3	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/12/08 18:2	29
-		access near memory)) and (trench via contact open\$3)) and etch\$3) and (source drain)) and resist\$6) and gate) and transistor) and ((pull?down (pull near3 down)) near10 transistor)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/12/08 18:2	
-		access near memory)) and (trench via contact open\$3)) and etch\$3) and (source drain)) and resist\$6) and gate) and transistor) and ((pull?down (pull near3	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB		
- :		access near memory)) and (trench via contact open\$3)) and etch\$3) and (source drain)) and resist\$6) and gate) and transistor) and ((pull?down (pull near3 down)) near10 transistor)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;		
-		access near memory)) and (trench via contact open\$3)) and etch\$3) and (source drain)) and resist\$6) and gate) and transistor) and ((pull?down (pull near3 down)) near10 transistor)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;		